ADVANCE

MICRON TECHNOLOGY INC

MT5C1008 883C

MILITARY SRAM

128K x 8 SRAM

T-46-23-14

FEATURES

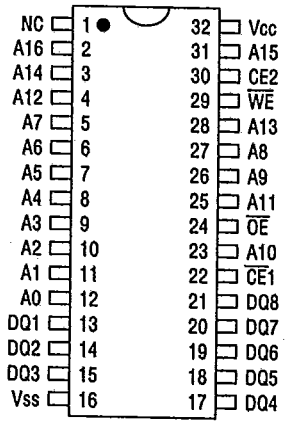
- High speed: 25, 30, 35, 45, and 55ns.
- Automatic chip enable power down
- All inputs and outputs are TTL compatible
- High performance, low power, CMOS process
- Single +5V (±10%) power supply
- Low power, ICC (max.) 70mA
- MIL-STD-883 Rev. C, Class B
- RAD tolerant (consult factory)

OPTIONS

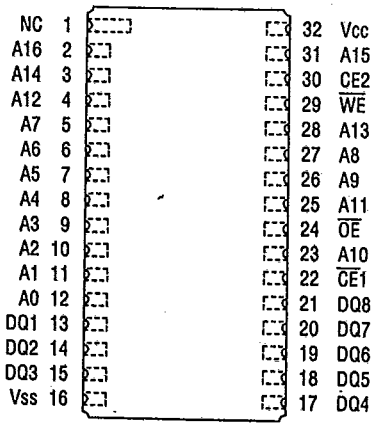
	MARKING
• Timing	
25ns access	-25
30ns access	-30
35ns access	-35
45ns access	-45
55ns access	-55
• Packages	
Ceramic DIP	C
Ceramic LCC	EC
• Two Volt Data Retention	L

PIN ASSIGNMENT (Top View)

32L/400/600 DIP



32L/LCC



GENERAL DESCRIPTION

The Micron SRAM family employs high speed, low power CMOS designs using a 4-transistor memory cell. They are fabricated using double layer metal, double layer polysilicon technology. All fabrication is 100% domestic.

For flexibility in high speed memory applications, Micron offers chip enable ($\overline{CE}$) on all organizations. Output enable ($\overline{OE}$) is an enhancement available and can place the output in a high impedance state for additional flexibility in system design.

Writing to these devices is accomplished when write enable ($\overline{WE}$) and $\overline{CE}$ inputs are both LOW. Reading is accomplished when $\overline{WE}$ remains HIGH and $\overline{CE}$ goes to LOW. $\overline{OE}$ must also be LOW to read the device. The devices offer a reduced power standby mode when disabled. This allows system designs for low power requirements.

All devices operate from a single +5V power supply and all inputs and outputs are fully TTL compatible.

FAST SRAM